36 Mb (1M x 36 & 2M x 18) QUAD (Burst of 2) Synchronous SRAMs



Features

- 1M x 36 or 2M x 18.
- On-chip delay-locked loop (DLL) for wide data valid window.
- Separate read and write ports with concurrent read and write operations.
- Synchronous pipeline read with early write operation.
- Double data rate (DDR) interface for read and write input ports.
- · Fixed 2-bit burst for read and write operations.
- · Clock stop support.
- Two input clocks (K and K) for address and control registering at rising edges only.
- Two input clocks (C and C) for data output control.

- Two echo clocks (CQ and CQ) that are delivered simultaneously with data.
- +1.8V core power supply and 1.5, 1.8V V_{DDQ}, used with 0.75, 0.9V V_{REF}
- · HSTL input and output levels.
- Registered addresses, write and read controls, byte writes, data in, and data outputs.
- · Full data coherency.
- Boundary scan using limited set of JTAG 1149.1 functions.
- · Byte write capability.
- · Fine ball grid array (FBGA) package
 - 15mm x 17mm body size
 - 1mm pitch
 - 165-ball (11 x 15) array
- Programmable impedance output drivers via 5x user-supplied precision resistor.

Description

The 36Mb IS61QDB21Mx36 and IS61QDB22Mx18 are synchronous, high-performance CMOS static random access memory (SRAM) devices. These These SRAMs have separate I/Os, eliminating the need for high-speed bus turnaround. The rising edge of K clock initiates the read/write operation, and all internal operations are self-timed. Refer to the *Timing Reference Diagram for Truth Table* on page 8 for a description of the basic operations of these SRAMs.

The input address bus operates at double data rate. The following are registered internally on the rising edge of the K clock:

- · Read address
- · Read enable
- · Write enable
- · Byte writes
- · Data-in for early writes

The following are registered on the rising edge of the \overline{K} clock:

- · Write address
- · Byte writes
- Data-in for second burst addresses

Byte writes can change with the corresponding data-in to enable or disable writes on a per-byte basis. An internal write buffer enables the data-ins to be registered half a cycle earlier than the write address. The first data-in burst is clocked at the same time as the write command signal, and the second burst is timed to the following rising edge of the \overline{K} clock.

During the burst read operation, the data-outs from the first burst are updated from output registers off the second rising edge of the \overline{C} clock (1.5 cycles later). The data-outs from the second burst are updated with the third rising edge of the C clock. The K and \overline{K} clocks are used to time the data-outs whenever the C and \overline{C} clocks are tied high.

The device is operated with a single +1.8V power supply and is compatible with HSTL I/O interfaces.



x36 FBGA Pinout (Top View)

	1	2	3	4	5	6	7	8	9	10	11
Α	CQ	V _{SS} /SA	NC/SA*	W	$\overline{\text{BW}}_2$	K	BW₁	R	SA	V _{SS} /SA	CQ
В	Q27	Q18	D18	SA	$\overline{\text{BW}}_3$	K	$\overline{\text{BW}}_0$	SA	D17	Q17	Q8
С	D27	Q28	D19	V_{SS}	SA	SA	SA	V_{SS}	D16	Q7	D8
D	D28	D20	Q19	V _{SS}	V _{SS}	V _{SS}	V_{SS}	V _{SS}	Q16	D15	D7
E	Q29	D29	Q20	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	Q15	D6	Q6
F	Q30	Q21	D21	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	D14	Q14	Q5
G	D30	D22	Q22	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	Q13	D13	D5
Н	Doff	V_{REF}	V_{DDQ}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	V_{DDQ}	V_{REF}	ZQ
J	D31	Q31	D23	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	D12	Q4	D4
K	Q32	D32	Q23	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	Q12	D3	Q3
L	Q33	Q24	D24	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	D11	Q11	Q2
М	D33	Q34	D25	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	D10	Q1	D2
N	D34	D26	Q25	V _{SS}	SA	SA	SA	V _{SS}	Q10	D9	D1
Р	Q35	D35	Q26	SA	SA	С	SA	SA	Q9	D0	Q0
R	TDO	TCK	SA	SA	SA	C	SA	SA	SA	TMS	TDI
	Note: The	following p	ins are rese	rved for higl	her densitie	s: A3 for 64	Mb, 10A for	144Mb, and	d 2A for 288	Mb.	

x18 FBGA Pinout (Top View)

	1	2	3	4	5	6	7	8	9	10	11
Α	CQ	V _{SS} /SA*	SA	W	$\overline{\text{BW}}_1$	K	NC	R	SA	V _{SS} /SA*	CQ
В	NC	Q9	D9	SA	NC	K	$\overline{\text{BW}}_0$	SA	NC	NC	Q8
С	NC	NC	D10	V_{SS}	SA	SA	SA	V_{SS}	NC	Q7	D8
D	NC	D11	Q10	V _{SS}	V _{SS}	V _{SS}	V_{SS}	V _{SS}	NC	NC	D7
Е	NC	NC	Q11	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC	D6	Q6
F	NC	Q12	D12	V_{DDQ}	V _{DD}	V _{SS}	V _{DD}	V_{DDQ}	NC	NC	Q5
G	NC	D13	Q13	V_{DDQ}	V _{DD}	V _{SS}	V _{DD}	V_{DDQ}	NC	NC	D5
Н	Doff	V _{REF}	V_{DDQ}	V_{DDQ}	V _{DD}	V _{SS}	V _{DD}	V_{DDQ}	V_{DDQ}	V _{REF}	ZQ
J	NC	NC	D14	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	Q4	D4
K	NC	NC	Q14	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	D3	Q3
L	NC	Q15	D15	V_{DDQ}	V _{SS}	V _{SS}	V_{SS}	V_{DDQ}	NC	NC	Q2
М	NC	NC	D16	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	NC	Q1	D2
Ν	NC	D17	Q16	V _{SS}	SA	SA	SA	V _{SS}	NC	NC	D1
Р	NC	NC	Q17	SA	SA	С	SA	SA	NC	D0	Q0
R	TDO	TCK	SA	SA	SA	C	SA	SA	SA	TMS	TDI
	Note: The	following p	ins are rese	rved for higl	her densitie	s: 10A for 7	2Mb and 2A	for 144Mb.			

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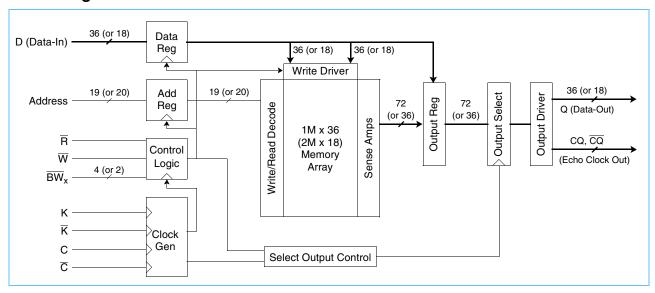


Pin Description

Symbol	Pin Number	Description
K, K	6B, 6A	Input clock.
C, \overline{C}	6P, 6R	Input clock for output data control.
CQ, CQ	11A, 1A	Output echo clock.
Doff	1H	DLL disable when low.
SA	9A, 4B, 8B, 5C, 6C, 7C, 5N, 6N, 7N, 4P, 5P, 7P, 8P, 3R, 4R, 5R, 7R, 8R, 9R	1M x 36 address inputs.
SA	3A, 9A, 4B, 8B, 5C, 6C, 7C, 5N, 6N, 7N, 4P, 5P, 7P, 8P, 3R, 4R, 5R, 7R, 8R, 9R	2M x 18 address inputs.
D0-D8 D9-D17 D18-D26 D27-D35	10P, 11N, 11M, 10K, 11J, 11G, 10E, 11D, 11C 10N, 9M, 9L, 9J, 10G, 9F, 10D, 9C, 9B 3B, 3C, 2D, 3F, 2G, 3J, 3L, 3M, 2N 1C, 1D, 2E, 1G, 1J, 2K, 1M, 1N, 2P	1M x 36 data inputs.
Q0–Q8 Q9–Q17 Q18–Q26 Q27–Q35	11P, 10M, 11L, 11K, 10J, 11F, 11E, 10C, 11B 9P, 9N, 10L, 9K, 9G, 10F, 9E, 9D, 10B 2B, 3D, 3E, 2F, 3G, 3K, 2L, 3N, 3P 1B, 2C, 1E, 1F, 2J, 1K, 1L, 2M, 1P	1M x 36 data outputs.
D0–D8 D9–D17	10P, 11N, 11M, 10K, 11J, 11G, 10E, 11D, 11C 3B, 3C, 2D, 3F, 2G, 3J, 3L, 3M, 2N	2M x 18 data inputs.
Q0–Q8 Q9–Q17	11P, 10M, 11L, 11K, 10J, 11F, 11E, 10C, 11B 2B, 3D, 3E, 2F, 3G, 3K, 2L, 3N, 3P	2M x 18 data outputs.
W	4A	Write control, active low.
R	8A	Read control, active low.
$\overline{BW}_{0,} \overline{BW}_{1,} \overline{BW}_{2,} \overline{BW}_{3}$	7B, 7A, 5A,5B	1M x 36 byte write control, active low.
$\overline{BW}_{0,} \overline{BW}_{1}$	7B, 5A	2M x 18 byte write control, active low.
V_{REF}	2H, 10H	Input reference level.
V_{DD}	5F, 7F, 5G, 7G, 5H, 7H, 5J, 7J, 5K, 7K	Power supply.
V_{DDQ}	4E,8E,4F,8F,4G,8G,3H,4H,8H,9H,4J,8J,4K,8K,4L,8L	Output power supply.
V _{SS}	2A, 10A, 4C, 8C, 4D, 5D, 6D, 7D, 8D, 5E, 6E, 7E, 6F, 6G, 6H, 6J, 6K, 5L, 6L, 7L, 4M, 5M, 6M, 7M, 8M, 4N, 8N	Power supply.
ZQ	11H	Output driver impedance control.
TMS, TDI, TCK	10R, 11R, 2R	IEEE 1149.1 test inputs (1.8V LVTTL levels).
TDO	1R	IEEE 1149.1 test output (1.8V LVTTL level).
NC	3A	1Mx36
NC	7A,1B,5B,9B,10B,1C,2C,9C,1D,9D,10D,1E,2E,9E,1F,9F,10F,1G, 9G,10G,1J,2J,9J,1K,2K,9K,1L,9L,10L,1M,2M,9M,1N,9N,10N,1P, 2P,9P	2Mx18



Block Diagram



SRAM Features

Read Operations

The SRAM operates continuously in a burst-of-two mode. Read cycles are started by registering \overline{R} in active low state at the rising edge of the K clock. A second set of clocks, C and \overline{C} , are used to control the timing to the outputs. A set of free-running echo clocks, CQ and \overline{CQ} , are produced internally with timings identical to the data-outs. The echo clocks can be used as data capture clocks by the receiver device.

When the C and \overline{C} clocks are connected high, the K and \overline{K} clocks assume the function of those clocks. In this case, the data corresponding to the first address is clocked 1.5 cycles later by the rising edge of the \overline{K} clock. The data corresponding to the second burst is clocked 2 cycles later by the following rising edge of the K clock.

A NOP operation (\overline{R} is high) does not terminate the previous read.

Write Operations

Write operations can also be initiated at every rising edge of the K clock whenever \overline{W} is low. The write address is provided 0.5 cycles later, registered by the rising edge of \overline{K} . Again, the write always occurs in bursts of two.

The write data is provided in an 'early write' mode; that is, the data-in corresponding to the first address of the burst, is presented 0.5 cycles earlier or at the rising edge of the preceding K clock. The data-in corresponding to the second write burst address follows next, registered by the rising edge of \overline{K} .

The data-in provided for writing is initially kept in write buffers. The information on these buffers is written into the array on the following write cycle. A read cycle to the last write address produces data from the write buffers. Similarly, a read address followed by the same write address produces the latest write data. The SRAM maintains data coherency.

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During a write, the byte writes independently control which byte of any of the two burst addresses is written (see X18/X36 Write Truth Tables on page 9 and Timing Reference Diagram for Truth Table on page 8).

Whenever a write is disabled (\overline{W} is high at the rising edge of K), data is not written into the memory.

RQ Programmable Impedance

An external resistor, RQ, must be connected between the ZQ pin on the SRAM and V_{SS} to enable the SRAM to adjust its output driver impedance. The value of RQ must be 5x the value of the intended line impedance driven by the SRAM. For example, an RQ of 250Ω results in a driver impedance of 50Ω . The allowable range of RQ to guarantee impedance matching is between 175Ω and 350Ω , with the tolerance described in *Programmable Impedance Output Driver DC Electrical Characteristics* on page 13. The RQ resistor should be placed less than two inches away from the ZQ ball on the SRAM module. The capacitance of the loaded ZQ trace must be less than 3 pF.

The ZQ pin can also be directly connected to V_{DDQ} to obtain a minimum impedance setting. ZQ must never be connected to V_{SS} .

Programmable Impedance and Power-Up Requirements

Periodic readjustment of the output driver impedance is necessary as the impedance is greatly affected by drifts in supply voltage and temperature. At power-up, the driver impedance is in the middle of allowable impedances values. The final impedance value is achieved within 1024 clock cycles.

Clock Consideration

This device uses an internal DLL for maximum output data valid window. It can be placed in a stopped-clock mode to minimize power and requires only 1024 cycles to restart.

No clocks can be issued until V_{DD} reaches its allowable operating range.

Single Clock Mode

This device can be also operated in single-clock mode. In this case, C and \overline{C} are both connected high at power-up and must never change. Under this condition, K and \overline{K} will control the output timings.

Either clock pair must have both polarities switching and must never connect to V_{REF} , as they are not differential clocks

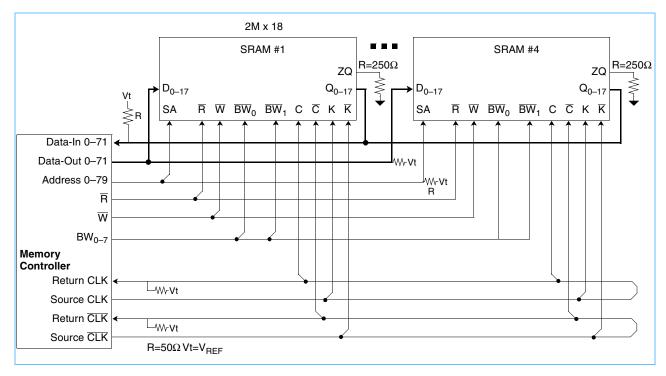
Depth Expansion

Separate input and output ports enable easy depth expansion, as each port can be selected and deselected independently. Read and write operations can occur simultaneously without affecting each other. Also, all pending read and write transactions are always completed prior to deselecting the corresponding port.

In the following application example, the second pair of C and \overline{C} clocks is delayed such that the return data meets the data setup and hold times at the bus master.



Application Example



Power-Up and Power-Down Sequences

The following sequence is used for power-up:

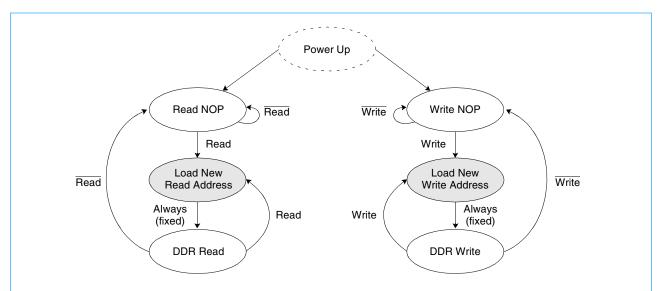
- 1. The power supply inputs must be applied in the following order while keeping Doff in LOW logic state:
 - 1) VDD
 - 2) VDDQ
 - 3) VREF
- 2. Start applying stable clock inputs $(K, \overline{K}, C, \text{ and } \overline{C})$.
- 3. After clock signals have stabilized, change Doff to HIGH logic state.
- 4. Once the Doff is switched to HIGH logic state, wait an additional 1024 clock cycles to lock the DLL.

NOTES

- 1. The power-down sequence must be done in reverse of the power-up sequence.
- 2. VDDQ can be allowed to exceed VDD by no more than 0.6V.
- 3. VREF can be applied concurrently with VDDQ.



State Diagram



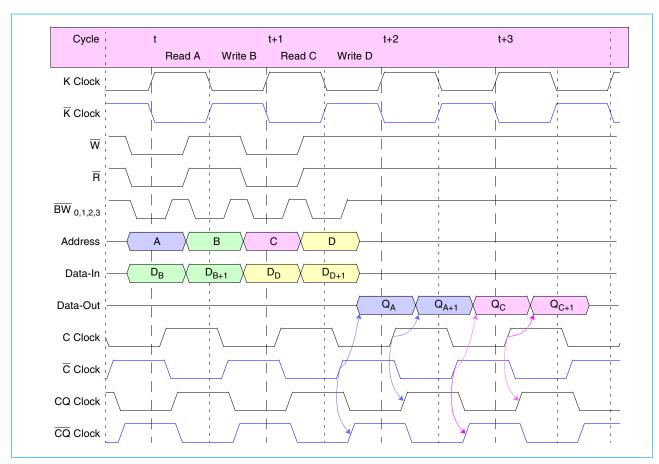
Notes: 1. Internal burst counter is fixed as two-bit linear; that is, when first address is A0+0, next internal burst address is A0+1.

- 2. Read refers to read active status with $\overline{R} = low$. Read refers to read inactive status with $\overline{R} = low$.
- 3. Write refers to write active status with $\overline{W} = low$. Write refers to write inactive status with $\overline{W} = high$.
- 4. The read and write state machines can be active simultaneously.
- 5. State machine control timing sequence is controlled by K.

The *Timing Reference Diagram for Truth Table* on page 8 is helpful in understanding the clock and write truth tables, as it shows the cycle relationship between clocks, address, data in, data out, and controls. All read and write commands are issued at the beginning of cycle "t".



Timing Reference Diagram for Truth Table



Clock Truth Table (Use the following table with the *Timing Reference Diagram for Truth Table*.)

Modo	Mode Clock Control		trols	Dat	a-In	Data-Out		
Mode	K	R	W	D _B	D _{B+1}	Q_A	Q _{A+1}	
Stop Clock	Stop	Х	Х	Previous state	Previous State	Previous state	Previous state	
No Operation (NOP)	L→H	Н	Н	Х	Х	High-Z	High-Z	
Read A	L→H	L	Х	х	х	D out at C (t + 1.5)	D out at C (t + 2)	
Write B	L→H	Х	L	D in at K (t)	D in at K (t + 0.5)	Х	Х	

Notes:

- 1. The internal burst counter is always fixed as two-bit.
- 2. X = don't care; H = logic "1"; L = logic "0".
- 3. A read operation is started when control signal $\overline{\mathsf{R}}$ is active low
- 4. A write operation is started when control signal \overline{W} is active low. Before entering into the stop clock, all pending read and write commands must be completed.
- 5. For timing definitions, refer to the *AC Characteristics* on page 15-16. Signals must have AC specifications at timings indicated in parenthesis with respect to switching clocks K, \overline{K} , C, and \overline{C} .



X36 Write Truth Table Use the following table with the *Timing Reference Diagram for Truth Table* on page 8.

Operation	K(t)	K (t + 0.5)	BW₀	BW₁	$\overline{\text{BW}}_2$	BW₃	D _B	D _{B+1}
Write Byte 0	L→H		L	Н	Н	Н	D0-8 (t)	
Write Byte 1	L→H		Н	L	Н	Н	D9-17 (t)	
Write Byte 2	L→H		Н	Н	L	Н	D18-26 (t)	
Write Byte 3	L→H		Н	Н	Н	L	D27-35 (t)	
Write All Bytes	L→H		L	L	L	L	D0-35 (t)	
Abort Write	L→H		Н	Н	Н	Н	Don't care	
Write Byte 0		L→H	L	Н	Н	Н		D0-8 (t + 0.5)
Write Byte 1		L→H	Н	L	Н	Н		D9-17 (t + 0.5)
Write Byte 2		L→H	Н	Н	L	Н		D18-26 (t + 0.5)
Write Byte 3		L→H	Н	Н	Н	L		D27-35 (t + 0.5)
Write All Bytes		L→H	L	L	L	L		D0-35 (t + 0.5)
Abort Write		L→H	Н	Н	Н	Н		Don't care

Notes:

- 1. For all cases. \overline{W} must be active low during the rising edge of K occurring at time t.
- 2. For timing definitions, refer to the *AC Characteristics* on page 15-16. Signals must have AC specifications with respect to switching clocks K and K.

X18 Write Truth Table (Use this table with the Timing Reference Diagram for Truth Table on page 8.)

Operation	K(t)	K (t + 0.5)	BW₀	BW₁	D _B	D _{B+1}
Write Byte 0 on B	L→H		L	Н	D0-8 (t)	
Write Byte 1 on B	L→H		Н	L	D9-17 (t)	
Write All Bytes on B	L→H		L	L	D0-17 (t)	
Abort Write on B	L→H		Н	Н	Don't care	
Write Byte 1 on B+1		L→H	L	Н		D0-8(t + 0.5)
Write Byte 2 on B+1		L→H	Н	L		D9-17(t + 0.5)
Write All Bytes on B+1		L→H	L	L		D0-17(t + 0.5)
Abort Write on B+1		L→H	Н	Н		Don't care

Notes

- 1. Refer to Timing Reference Diagram for Truth Table on page 8. Cycle time starts at n and is referenced to the K clock.
- 2. For all cases, \overline{W} must be active low during the rising edge of K occurring at t.
- 3. For timing definitions, refer to the *AC Characteristics* on page 15-16. Signals must have AC specs with respect to switching clocks K and \overline{K} .



Absolute Maximum Ratings

Item	Symbol	Rating	Units
Power supply voltage	VDD	-0.5 to 2.6	V
Output power supply voltage	VDDQ	-0.5 to 2.6	V
Input voltage	VIN	-0.5 to 2.6	V
Data out voltage	VDOUT	-0.5 to 2.6	V
Junction temperature	TJ	110	°C
Storage temperature	TSTG	-55 to +125	°C

Note: Stresses greater than those listed in this table can cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this datasheet is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Operating Temperature Range

Range	Symbol	Rating	Unit
Commercial	TA	0 to 70	°C
Industrial	TA	-40 to +85	°C

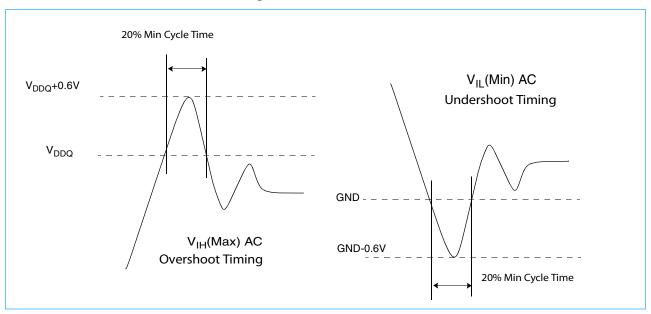


Recommended DC Operating Conditions (Over the operating temperature)

Parameter	Symbol	Minimum	Typical	Maximum	Units	Notes
Supply voltage	V_{DD}	1.8 - 5%		1.8 + 5%	V	1
Output driver supply voltage	V_{DDQ}	1.4		1.9	V	1
Input high voltage	V _{IH}	V _{REF} +0.1		V _{DDQ} + 0.3	V	1, 2
Input low voltage	V _{IL}	-0.3		V _{REF} - 0.1	V	1, 3
Input reference voltage	V _{REF}	0.68		0.95	V	1, 5
Clocks signal voltage	V _{IN - CLK}	-0.3		V _{DDQ} + 0.3	V	1, 4

- 1. All voltages are referenced to $\rm V_{SS}.$ All $\rm V_{DD},\,V_{DDQ},$ and $\rm V_{SS}$ pins must be connected.
- 2. V_{IH}(Max) AC = See *0vershoot and Undershoot Timings*.
- 3. V_{IL}(Min) AC = See *0vershoot and Undershoot Timings*.
- 4. $V_{\text{IN-CLK}}$ specifies the maximum allowable DC excursions of each clock (K, $\overline{\text{K}}$, C, and $\overline{\text{C}}$).
- 5. Peak-to-peak AC component superimposed on V_{REF} may not exceed 5% of V_{REF}

Overshoot and Undershoot Timings



PBGA Thermal Characteristics

Item	Symbol	Rating	Units
Thermal resistance junction to ambient (airflow = 1m/s)	ROJA	20.4	° C/W
Thermal resistance junction to case	RejiC	4.0	° C/W
Thermal resistance junction to pins	Røjb	3.23	°C/W



Capacitance ($V_{DD} = 1.8V - 5\%$, +5%, f = 1MHz. Over the operating temperature range.)

Parameter	Symbol	Test Condition	Maximum	Units
Input capacitance	C _{IN}	$V_{IN} = 0V$	4	pF
Data-in capacitance (D0–D35)	C _{DIN}	$V_{DIN} = 0V$	4	pF
Data-out capacitance (Q0-Q35)	C _{OUT}	V _{OUT} = 0V	4	pF
Clocks Capacitance (K, K, C, C				

DC Electrical Characteristics (V_{DD} = 1.8V -5%, +5%. Over the operating temperature range.)

Parameter	Symbol	Minimum	Maximum	Units	Notes
x36 average power supply operating current $(I_{OUT} = 0, V_{IN} = V_{IH} \text{ or } V_{IL})$	I _{DD30} I _{DD40} 1 I _{DD50}	_	800 700 600	mA	1, 3
x18 average power supply operating current $(I_{OUT} = 0, V_{IN} = V_{IH} \text{ or } V_{IL})$	I _{DD30} I _{DD40} 1 I _{DD50}	_	800 700 600	mA	1, 3
Power supply standby current $(\overline{R} = V_{IH}, \overline{W} = V_{IH}.$ All other inputs = V_{IH} or V_{IH} , $I_{IH} = 0$)	I _{SBSS}	_	200	mA	1
Input leakage current, any input (except JTAG) (V _{IN} = V _{SS} or V _{DD})	l _{LI}	-2	+2	uA	
Output leakage current (V _{OUT} = V _{SS} or V _{DDQ} , Q in High-Z)	I _{LO}	-5	+5	uA	
Output "high" level voltage (I _{OH} = -6mA)	V _{OH}	V _{DDQ} -0.4	V_{DDQ}	V	2, 4
Output "low" level voltage (I _{OL} = +6mA)	V _{OL}	V _{SS}	V _{SS} +0.4	V	2, 4
JTAG leakage current (V _{IN} = V _{SS} or V _{DD})	I _{LIJTAG}	-100	+100	uA	5

^{1.} I_{OUT} = chip output current.

^{2.} Minimum impedance output driver.

^{3.} The numeric suffix indicates the part operating at speed, as indicated in *AC Characteristics* on page 15-16 (that is, I_{DD25} indicates 2.5ns cycle time).

^{4.} JEDEC Standard JESD8-6 Class 1 compatible.

^{5.} For JTAG inputs only.

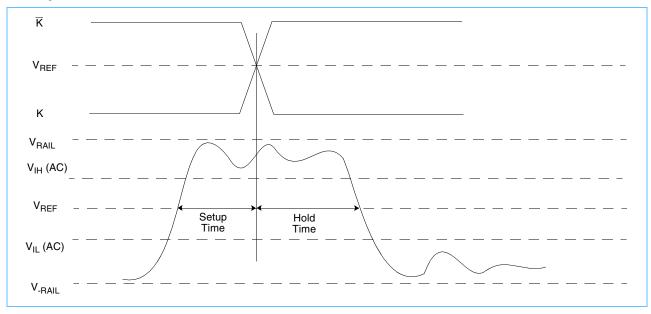


Typical AC Input Characteristics

Item	Symbol	Minimum	Maximum	Notes
AC input logic high	V _{IH} (ac)	V _{REF} + 0.2		1, 2, 3, 4
AC input logic low	V _{IL} (ac)		V _{REF} - 0.2	1, 2, 3, 4
Clock input logic high (K, \overline{K} , C, \overline{C})	V _{IH-CLK} (ac)	V _{REF} + 0.2		1, 2, 3
Clock input logic low (K, K, C, C)	V _{IL-CLK} (ac)		V _{REF} - 0.2	1, 2, 3

- 1. The peak-to-peak AC component superimposed on V_{REF} may not exceed 5% of the DC component of V_{REF} .
- 2. Performance is a function of V_{IH} and V_{IL} levels to clock inputs.
- 3. See the AC Input Definition diagram.
- 4. See the AC Input Definition diagram. The signals should swing monotonically with no steps rail-to-rail with input signals never ringing back past VIH (AC) and VIL (AC) during the input setup and input hold window. VIH (AC) and VIL (AC) are used for timing purposes only.

AC Input Definition



Programmable Impedance Output Driver DC Electrical Characteristics

 $(V_{DD} = 1.8V - 5\%, +5\%, V_{DDQ} = 1.5, 1.8V$. Over the operating temperature range.)

Parameter	Symbol	Minimum	Maximum	Units	Notes
Output "high" level voltage	V _{OH}	V _{DDQ} / 2	V_{DDQ}	V	1, 3
Output "low" level voltage	V _{OL}	V_{SS}	V _{DDQ} / 2	V	2, 3

1.
$$I_{OH} = \left(\frac{VDDQ}{2}\right) / \left(\frac{RQ}{5}\right) \pm 15\%$$
 @ $V_{OH} = V_{DDQ} / 2$ For: $175\Omega \le RQ \le 350\Omega$

2.
$$I_{OL} = \left(\frac{\text{VDDQ}}{2}\right) / \left(\frac{\text{RQ}}{5}\right) \pm 15\% @ V_{OL} = V_{DDQ} / 2 \text{ For: } 175\Omega \le \text{RQ} \le 350\Omega$$

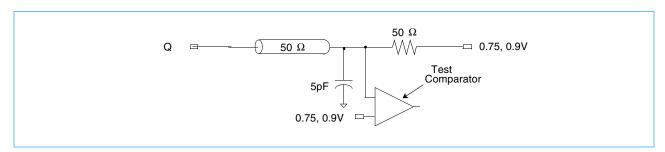
3. Parameter tested with RQ = 250Ω and V_{DDQ} = 1.5V.



AC Test Conditions (V_{DD} = 1.8V -5%, +5%, V_{DDQ} = 1.5, 1.8V. Over the operating temperature range.)

Parameter	Symbol	Conditions	Units	Notes
Output driver supply voltage	V_{DDQ}	1.5, 1.8	V	
Input high level	V _{IH}	1.25	V	
Input Low Level	V _{IL}	0.25	V	
Input reference voltage	V_{REF}	0.75	V	
Input rise time	T _R	0.35	ns	
Input fall time	T _F	0.35	ns	
Output timing reference level		V _{DDQ/2}	V	
Output load conditions				1, 2
 See AC Test Loading. Parameter tested with RQ = 250 and V_{DDQ} = 1.5V. 				

AC Test Loading



36 Mb (1M x 36 & 2M x 18) QUAD (Burst of 2) Synchronous SRAMs



AC Characteristics (V_{DD} = 1.8V -5%, +5%. Over the operating temperature range.)

Parameter	Symbol	300N (300N		Units	Notes
		Min	Max		
Clock					
Cycle time (K, \overline{K} , C, \overline{C})	t _{KHKH}	3.3	7.5	ns	
Clock phase jitter (K, \overline{K} , C, \overline{C})	t _{KC-VAR}		0.12	ns	
Clock high pulse (K, \overline{K} , C, \overline{C})	t _{KHKL}	1.32		ns	
Clock low pulse (K, \overline{K} , C, \overline{C})	t _{KLKH}	1.32		ns	
Clock to $\overline{\text{clock}}$ (K _H > $\overline{\text{K}}_{\text{H}}$, C _H > $\overline{\text{C}}_{\text{H}}$)	t _{KHK̄H}	1.35		ns	
Clock to data clock $(K_H > C_H, \overline{K}_H > \overline{C}_H)$	t _{KHCH}	0.0	1.35	ns	
DLL lock (K, C)	t _{KC-lock}	1024		cycle	
K static to DLL reset	t _{KC-reset}	30		ns	
Output Times					
C, C high to output valid	t _{CHQV}		0.40	ns	1, 3
C, C high to output hold	t _{CHQX}	-0.40		ns	1, 3
C, C high to echo clock valid	t _{CHCQV}		0.35	ns	3
C, C high to echo clock hold	t _{CHCQX}	-0.35		ns	3
CQ, CQ high to output valid	t _{CQHQV}		0.25	ns	1, 3
CQ, CQ high to output hold	t _{CQHQX}	-0.25		ns	1, 3
C high to output high-Z	t _{CHQZ}		0.33	ns	1, 3
C high to output low-Z	t _{CHQX1}	-0.33		ns	1, 3
Setup Times					
Address valid to K, K rising edge	t _{AVKH}	0.33	_	ns	2
Control inputs valid to K rising edge	t _{IVKH}	0.33	_	ns	2
Data-in valid to K, K rising edge	t _{DVKH}	0.33	_	ns	2
Hold Times					
K rising edge to address hold	t _{KHAX}	0.33	_	ns	2
K rising edge to control inputs hold	t _{KHIX}	0.33	_	ns	2
K, K rising edge to data-in hold	t _{KHDX}	0.33	_	ns	2

^{1.} See AC Test Loading on page 14.

 $^{2. \ \, \}text{During normal operation, V}_{IH}, \, \text{V}_{IL}, \, \text{T}_{RISE}, \, \text{and T}_{FALL} \, \, \text{of inputs must be within 20\% of V}_{IH}, \, \text{V}_{IL}, \, \text{T}_{RISE}, \, \text{and T}_{FALL} \, \, \text{of clock.}$

^{3.} If C, \overline{C} are tied high, then K, \overline{K} become the references for C, \overline{C} timing parameters.



AC Characteristics (V_{DD} = 1.8V -5%, +5%. Over the operating temperature range.)

Parameter	Symbol	4((250N		50 ⁴ (200MHz)		Units	Notes
		Min	Max	Min	Max		
Clock							
Cycle time (K, \overline{K} , C, \overline{C})	t _{KHKH}	4.0	7.5	5.0	7.5	ns	
Clock phase jitter (K, K, C, C)	t _{KC-VAR}		0.2		0.2	ns	
Clock high pulse (K, \overline{K} , C, \overline{C})	t _{KHKL}	1.6		2.0		ns	
Clock low pulse (K, \overline{K} , C, \overline{C})	t _{KLKH}	1.6		2.0		ns	
Clock to $\overline{\text{clock}}$ (K _H > $\overline{\text{K}}_{\text{H}}$, C _H > $\overline{\text{C}}_{\text{H}}$)	t _{KHK} H	1.8		2.2		ns	
Clock to data clock $(K_H > C_H, \overline{K}_H > \overline{C}_H)$	t _{KHCH}	0.0	1.35	0.0	1.35	ns	
DLL lock (K, C)	t _{KC-lock}	1024		1024		cycle	
K static to DLL reset	t _{KC-reset}	30		30		ns	
Output Times							
C, \overline{C} high to output valid	t _{CHQV}		0.45		0.45	ns	1, 3
C, \overline{C} high to output hold	t _{CHQX}	-0.45		-0.45		ns	1, 3
C, \overline{C} high to echo clock valid	t _{CHCQV}		0.40		0.4	ns	3
C, \overline{C} high to echo clock hold	t _{CHCQX}	-0.40		-0.40		ns	3
CQ, CQ High to output valid	t _{CQHQV}		0.30		0.40	ns	1, 3
CQ, CQ high to output hold	t _{CQHQX}	-0.30		-0.40		ns	1, 3
C High to output high-Z	t _{CHQZ}		0.35		0.38	ns	1, 3
C High to output low-Z	t _{CHQX1}	-0.35		-0.38		ns	1, 3
Setup Times							
Address valid to K, \overline{K} rising edge	t _{AVKH}	0.35	_	0.4	_	ns	2
Control inputs valid to K rising edge	t _{IVKH}	0.35	_	0.4	_	ns	2
Data-in valid to K, K rising edge	t _{DVKH}	0.35	_	0.4	_	ns	2
Hold Times							
K rising edge to address hold	t _{KHAX}	0.35	_	0.4	_	ns	2
K rising edge to Control Inputs Hold	t _{KHIX}	0.35	_	0.4	_	ns	2
K, \overline{K} rising edge to data-in hold	t _{KHDX}	0.35	_	0.4	_	ns	2

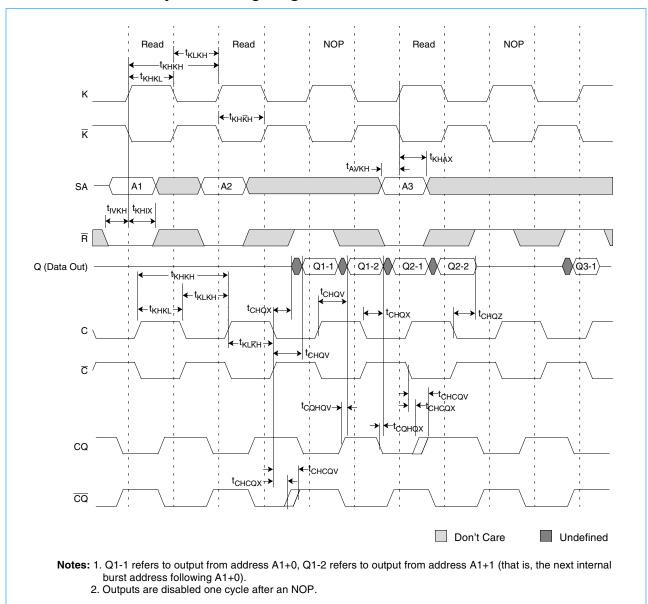
^{1.} See AC Test Loading on page 14.

 $^{2. \ \, \}text{During normal operation, V}_{IH}, \, \text{V}_{IL}, \, \text{T}_{RISE}, \, \text{and T}_{FALL} \, \, \text{of inputs must be within 20\% of V}_{IH}, \, \text{V}_{IL}, \, \text{T}_{RISE}, \, \text{and T}_{FALL} \, \, \text{of clock.}$

^{3.} If C, \overline{C} are tied high, then K, \overline{K} become the references for C, \overline{C} timing parameters.

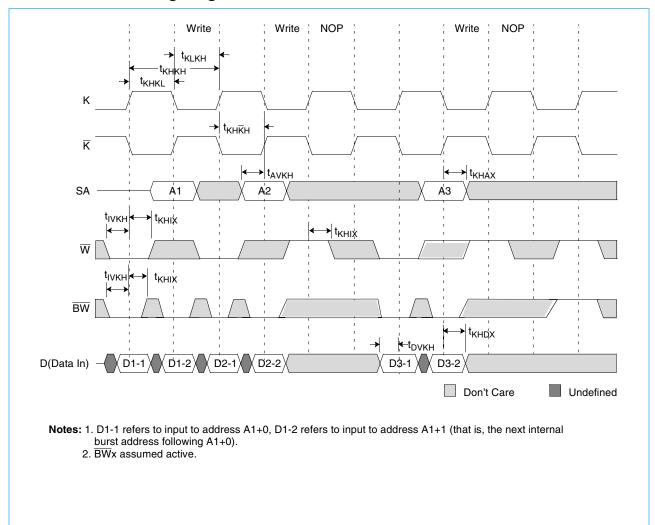


Read and Deselect Cycles Timing Diagram



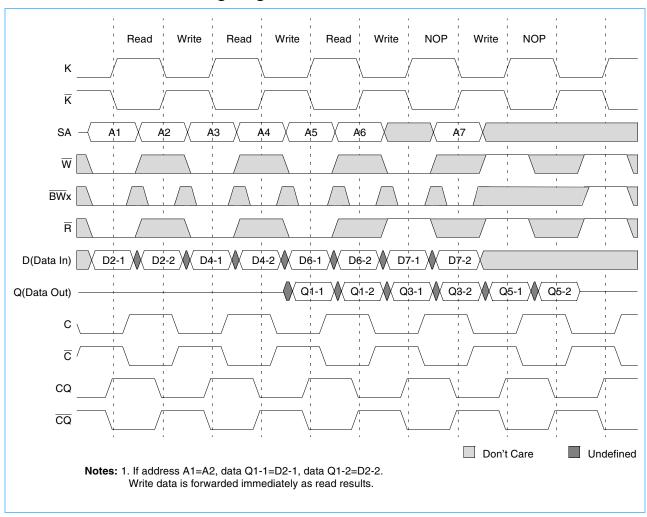


Write and NOP Timing Diagram





Read, Write, and NOP Timing Diagram





IEEE 1149.1 TAP and Boundary Scan

The SRAM provides a limited set of JTAG functions to test the interconnection between SRAM I/Os and printed circuit board traces or other components. There is no multiplexer in the path from I/O pins to the RAM core.

In conformance with IEEE Standard 1149.1, the SRAM contains a TAP controller, instruction register, boundary scan register, bypass register, and ID register.

The TAP controller has a standard 16-state machine that resets internally on power-up. Therefore, a TRST signal is not required.

Signal List

· TCK: test clock

· TMS: test mode select

TDI: test data-inTDO: test data-out

JTAG DC Operating Characteristics (Over the operating temperature range.) Operates with JEDEC Standard 8-5 (1.8V) logic signal levels

Parameter	Symbol	Minimum	Typical	Maximum	Units	Notes
JTAG input high voltage	V _{IH1}	1.3	_	V _{DD} +0.3	V	1
JTAG input low voltage	V _{IL1}	-0.3	_	0.5	V	1
JTAG output high level	V _{OH1}	V _{DD} -0.4	_	V_{DD}	V	1, 2
JTAG output low level	V _{OL1}	V_{SS}	_	0.4	V	1, 3

^{1.} All JTAG inputs and outputs are LVTTL-compatible.

JTAG AC Test Conditions (V_{DD} = 1.8V -5%, +5%. Over the operating temperature range)

Parameter	Symbol	Conditions	Units
Input pulse high level	V _{IH1}	1.3	V
Input pulse low level	V _{IL1}	0.5	V
Input rise time	T _{R1}	1.0	ns
Input fall time	T _{F1}	1.0	ns
Input and output timing reference level		0.9	V

^{2.} $I_{OH1} \ge -I2mAI$

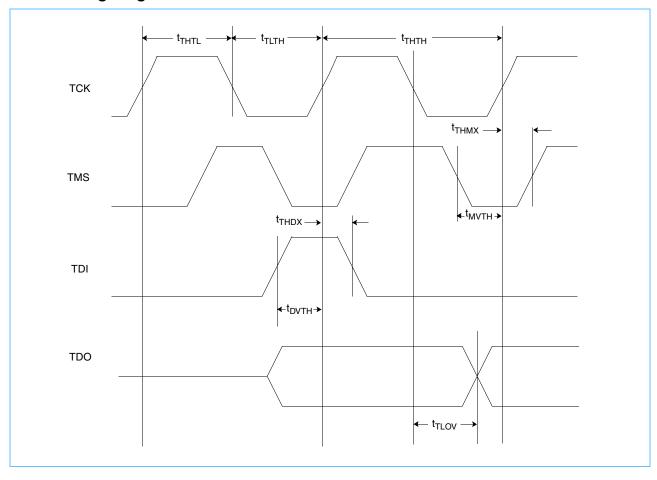
^{3.} $I_{OL1} \ge +|2mA|$.



JTAG AC Characteristics ($V_{DD} = 1.8V - 5\%$, +5%. Over the operating temperature range.)

Parameter	Symbol	Minimum	Maximum	Units	Notes
TCK cycle time	t _{THTH}	20	_	ns	
TCK high pulse width	t _{THTL}	7	_	ns	
TCk low pulse width	t _{TLTH}	7	_	ns	
TMS setup	t _{MVTH}	4	_	ns	
TMS hold	t _{THMX}	4	_	ns	
TDI setup	t _{DVTH}	4	_	ns	
TDI hold	t _{THDX}	4	_	ns	
TCK low to valid data	t _{TLOV}	_	7	ns	1
1. See AC Test Loading on page 14.					

JTAG Timing Diagram





Scan Register Definition

Register Name	Bit Size x18 or x36
Instruction	3
Bypass	1
ID	32
Boundary Scan	109

ID Register Definition

		Field Bit Number and Descrip	Field Bit Number and Description				
Part	Revision Number (31:29)	Part Configuration (28:12)	JEDEC Code (11:1)	Start Bit (0)			
2M x 18	000	00def0wx0t0q0b0s0	000 101 001 00	1			
1M x 36	000	00def0wx0t0q0b0s0	000 101 001 00	1			

Part Configuration Definition:

def = 010 for 36Mb

wx = 11 for x36, 10 for x18

t = 1 for DLL, 0 for non-DLL

q = 1 for QDB2, 0 for DDR

b = 1 for burst of 4, 0 for burst of 2

s = 1 for separate I/0, 0 for common I/O



Instruction Set

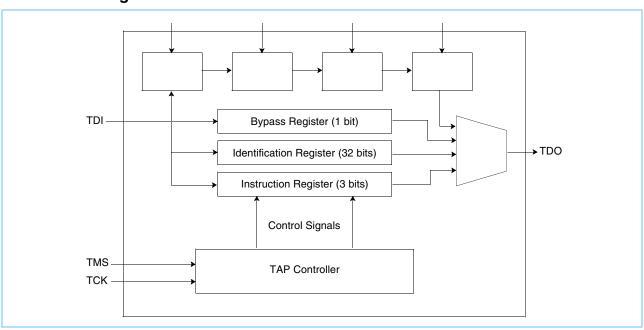
Code	Instruction	TDO Output	Notes
000	EXTEST	Boundary Scan Register	2,6
001	IDCODE	32-bit Identification Register	
010	SAMPLE-Z	Boundary Scan Register	1, 2
011	PRIVATE	Do not use	5
100	SAMPLE	Boundary Scan Register	4
101	PRIVATE	Do not use	5
110	PRIVATE	Do not use	5
111	BYPASS	Bypass Register	3

- 1. Places Qs in high-Z in order to sample all input data, regardless of other SRAM inputs.
- 2. TDI is sampled as an input to the first ID register to allow for the serial shift of the external TDI data.
- 3. BYPASS register is initiated to V_{SS} when BYPASS instruction is invoked. The BYPASS register also holds the last serially loaded TDI when exiting the shift-DR state.
- 4. SAMPLE instruction does not place DQs in high-Z.
- 5. This instruction is reserved. Invoking this instruction will cause improper SRAM functionality.
- 6. This EXTEST is not IEEE 1149.1-compliant. By default, it places Q in high-Z. If the internal register on the scan chain is set high, Q will be updated with information loaded via a previous SAMPLE instruction. The actual transfer occurs during the update IR state after EXTEST is loaded. The value of the internal register can be changed during SAMPLE and EXTEST only.

List of IEEE 1149.1 Standard Violations

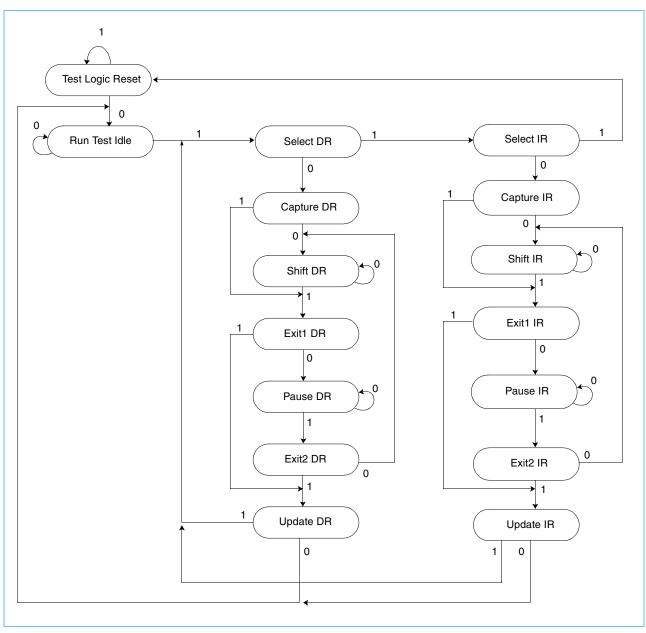
- 7.2.1.b, e
- 7.7.1.a-f
- 10.1.1.b, e
- 10.7.1.a-d
- 6.1.1.d

JTAG Block Diagram





TAP Controller State Machine





Order	Pin ID
1	6R
2	6P
3	6N
4	7P
5	7N
6	7R
7	8R
8	8P
9	9R
10	11P
11	10P
12	10N
13	9P
14	10M
15	11N
16	9M
17	9N
18	11L
19	11M
20	9L
21	10L
22	11K
23	10K
24	9J
25	9K
26	10J
27	11J
28	11H
29	10G
30	9G
31	11F
32	11G
33	9F
34	10F
35	11E
36	10E

Order	Pin ID		
37	10D		
37	9E		
39	10C		
40	11D		
41	9C		
42	9D		
43	11B		
44	11C		
45	9B		
46	10B		
47	11A		
48	10A		
49	9A		
50	8B		
51	7C		
52	6C		
53	8A		
54	7A		
55	7B		
56	6B		
57	6A		
58	5B		
59	5A		
60	4A		
61	5C		
62	4B		
63	ЗА		
64	2A		
65	1A		
66	2B		
67	3B		
68	1C		
69	1B		
70	3D		
71	3C		
72	1D		

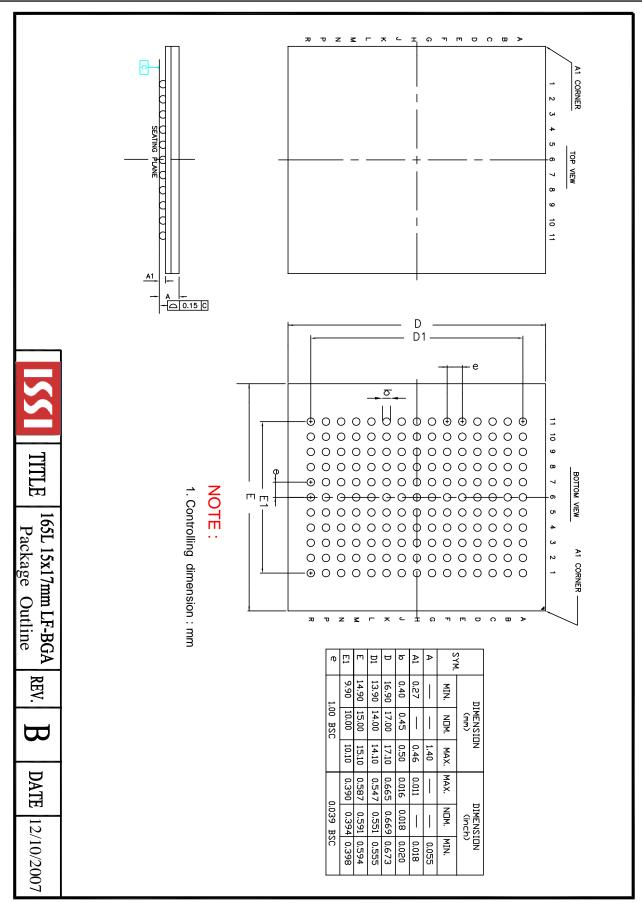
	I		
Order	Pin ID		
73	2C		
74	3E		
75	2D		
76	2E		
77	1E		
78	2F		
79	3F		
80	1G		
81	1F		
82	3G		
83	2G		
84	1H		
85	1J		
86	2J		
87	зК		
88	3J		
89	2K		
90	1K		
91	2L		
92	3L		
93	1M		
94	1L		
95	3N		
96	ЗМ		
97	1N		
98	2M		
99	3P		
100	2N		
101	2P		
102	1P		
103	3R		
104	4R		
105	4P		
106	5P		
107	5N		
108	5R		
109	Internal		
-			

Note

¹⁾ NC pins as defined on FBGA pinouts on page 2 are read as "don't cares".

²⁾ State of Internal pin (#109) is loaded via JTAG







ORDERING INFORMATION:

Commercial Range: 0°C to +70°C

Speed	Order Part No.	Organization	Package	
300 MHz	IS61QDB21M36-300M3	1Mx36	165 BGA	
	IS61QDB21M36-300M3L	1Mx36	165 BGA, Lead-free	
	IS61QDB22M18-300M3	2Mx18	165 BGA	
	IS61QDB22M18-300M3L	2Mx18	165 BGA, Lead-free	
250 MHz	IS61QDB21M36-250M3	1Mx36	165 BGA	
	IS61QDB21M36-250M3L	1Mx36	165 BGA, Lead-free	
	IS61QDB22M18-250M3	2Mx18	165 BGA	
	IS61QDB22M18-250M3L	2Mx18	165 BGA, Lead-free	

Industrial Range: -40°C to +85°C

Speed	Order Part No.	Organization	Package
300 MHz	IS61QDB21M36-300M3I	1Mx36	165 BGA
	IS61QDB21M36-300M3LI	1Mx36	165 BGA, Lead-free
	IS61QDB22M18-300M3I	2Mx18	165 BGA
	IS61QDB22M18-300M3LI	2Mx18	165 BGA, Lead-free
250 MHz	IS61QDB21M36-250M3I	1Mx36	165 BGA
	IS61QDB21M36-250M3LI	1Mx36	165 BGA, Lead-free
	IS61QDB22M18-250M3I	2Mx18	165 BGA
	IS61QDB22M18-250M3LI	2Mx18	165 BGA, Lead-free

Speed	Top Mark	Order Part No.	Org.	Package
200 MHz	IS61QDB22M18-250M3	U757A-200M3I*	2Mx18	165 BGA
	IS61QDB22M18-250M3L	U757A-200M3LI*	2Mx18	165 BGA, Lead-free
	IS61QDB21M36-250M3	U757D-200M3I*	1Mx36	165 BGA
	IS61QDB21M36-250M3L	U757D-200M3LI*	1Mx36	165 BGA, Lead-free

Note

^{*} These parts are fully tested to Industrial temperature, even though the top mark is Commercial. By ordering these parts, the customer will receive parts that are tested to the Industrial Temperature of -40°C to +85°C. The speed will be 200MHz at -40°C to +85°C.

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IS66WVE4M16ECLL-70BLI PCF8570P K6T4008C1B-GB70 CY7C1353S-100AXC AS6C8016-55BIN 515712X IS62WV51216EBLL45BLI IS63WV1288DBLL-10HLI IS66WVE2M16ECLL-70BLI 47L16-E/SN IS66WVE4M16EALL-70BLI IS62WV6416DBLL-45BLI
IS61WV102416DBLL-10TLI CY7C1381KV33-100AXC CY7C1381KV33-100BZXI CY7C1373KV33-100AXC CY7C1381KVE33-133AXI
CY7C4042KV13-933FCXC 8602501XA 5962-3829425MUA 5962-8855206YA 5962-8866201XA 5962-8866201YA 5962-8866204TA
5962-8866206MA 5962-8866207NA 5962-8866208UA 5962-8872502XA 5962-8959836MZA 5962-8959841MZA 5962-9062007MXA
5962-9161705MXA N08L63W2AB7I 7130LA100PDG GS882Z18CD-150I GS81284Z36B-250I M38510/28902BVA IS62WV12816ALL70BLI 5962-8971203XA